

Fig. 1

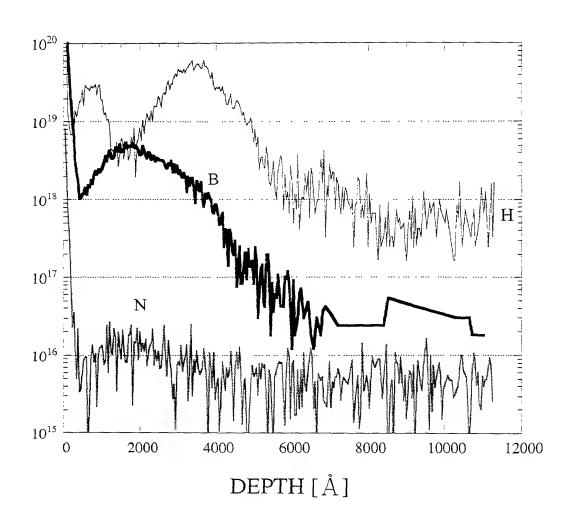


Fig. 2

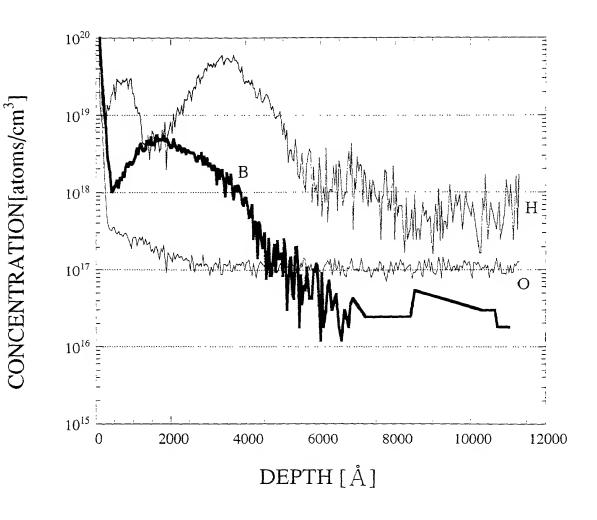
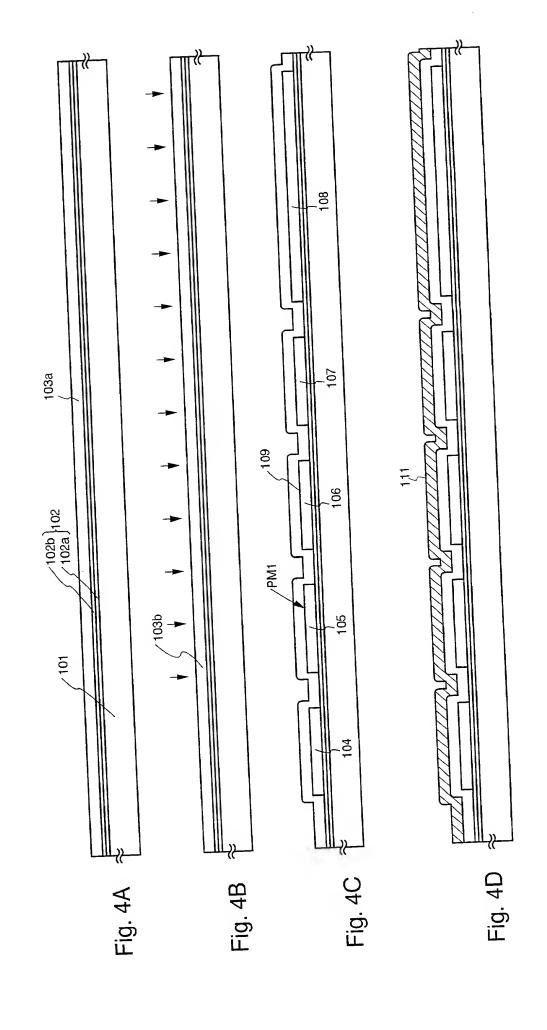
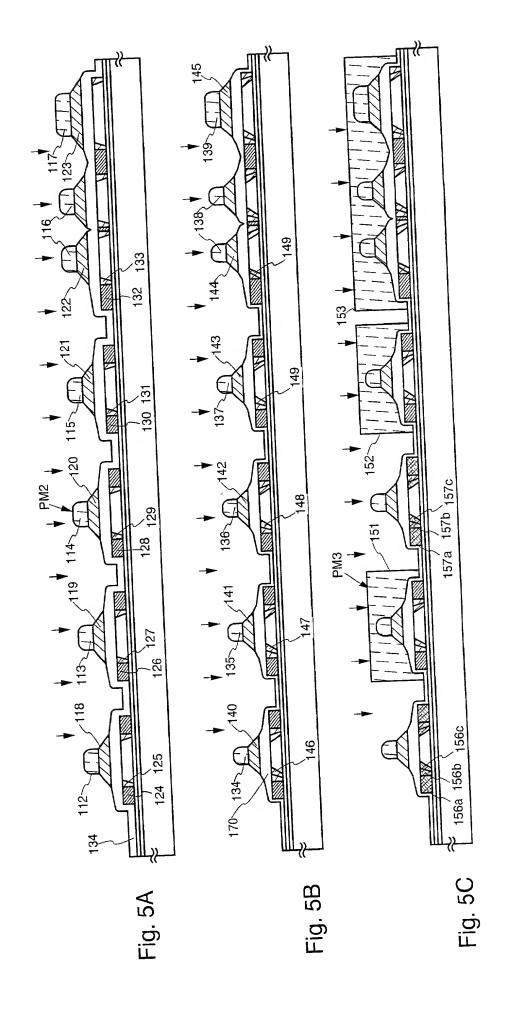
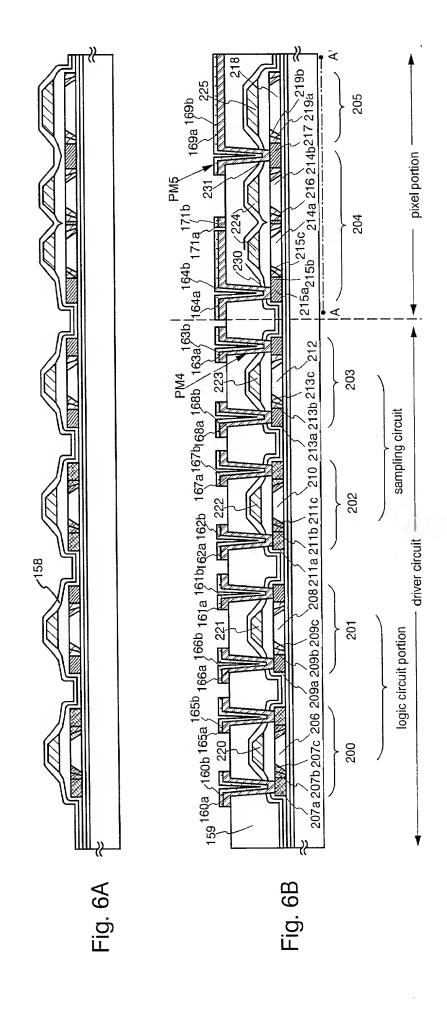


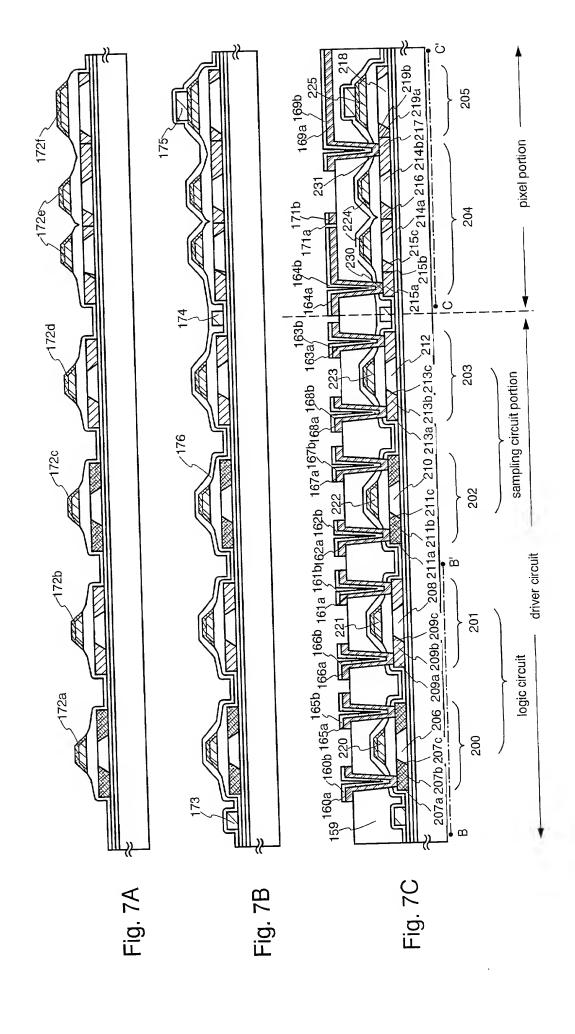
Fig. 3

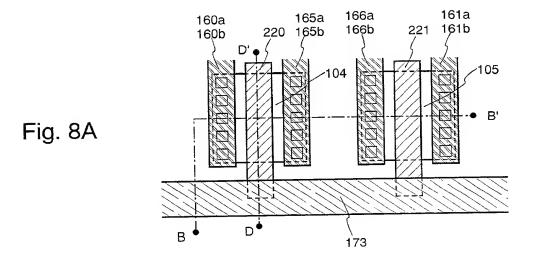
ii (**iii** (ii

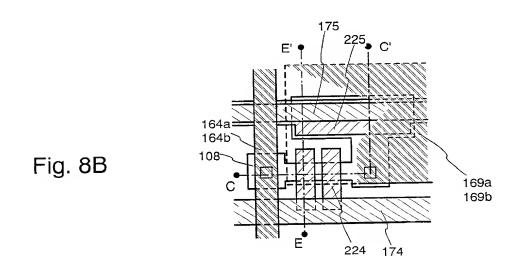


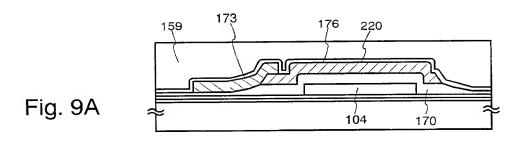


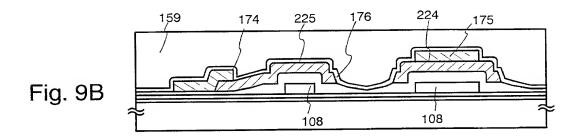


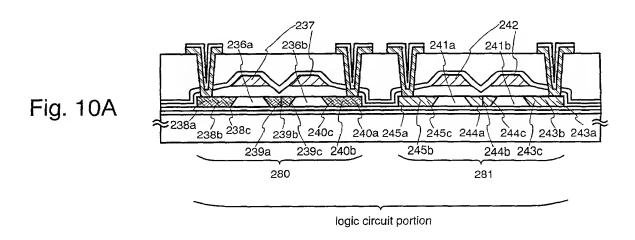


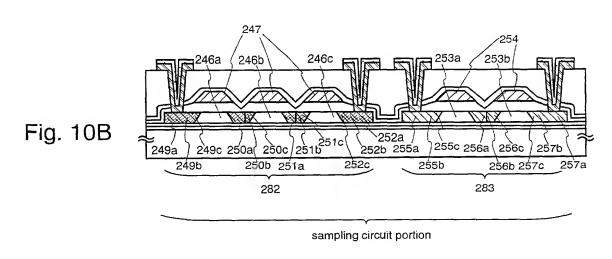


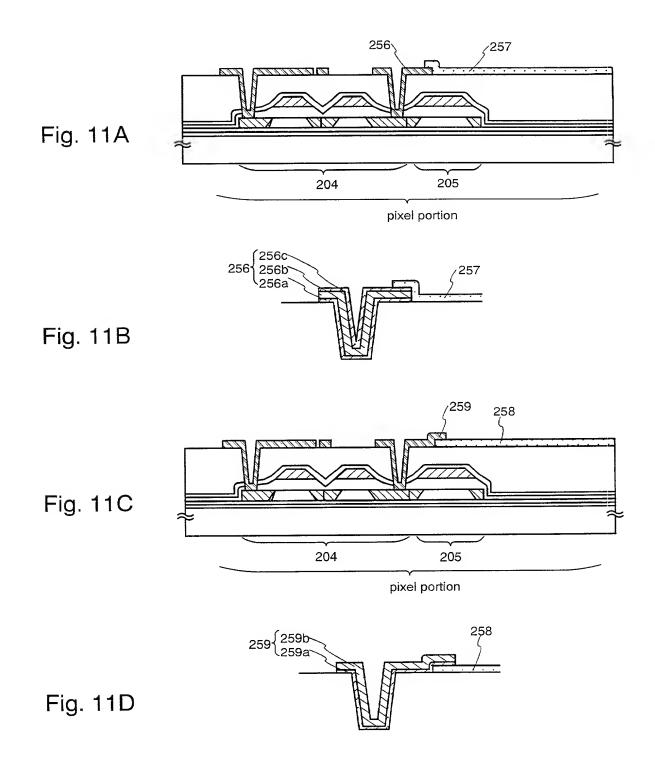












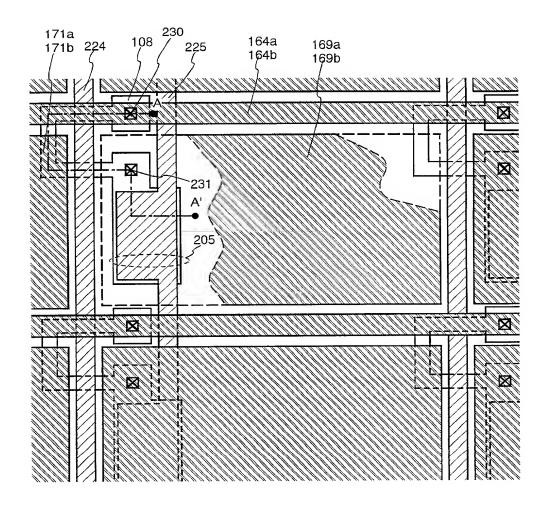
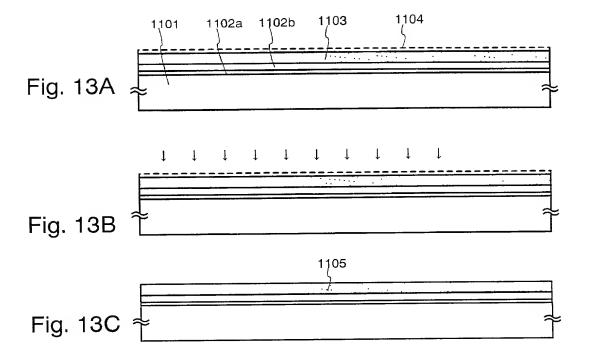


Fig. 12



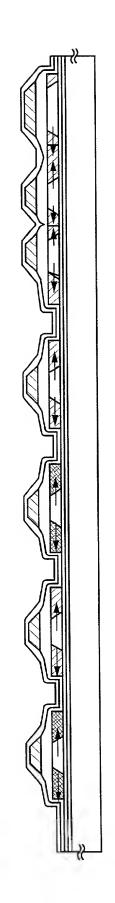


Fig. 14

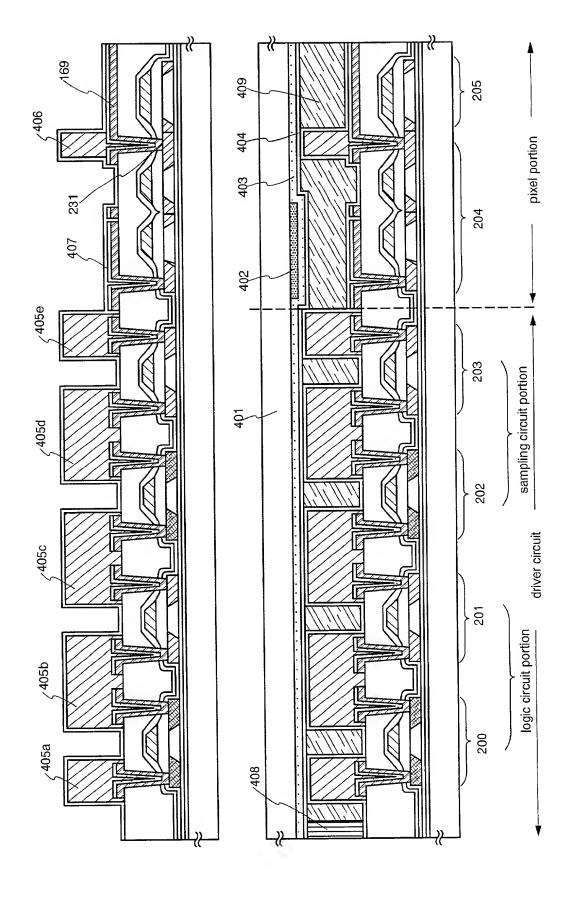


Fig. 15

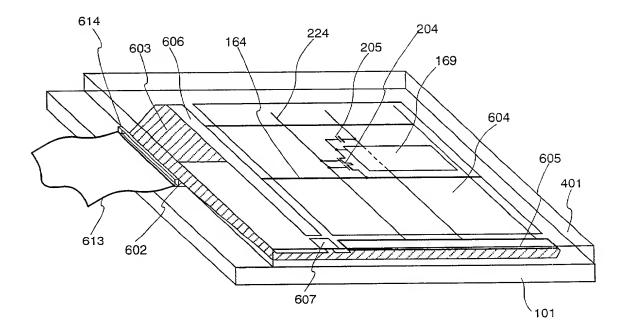
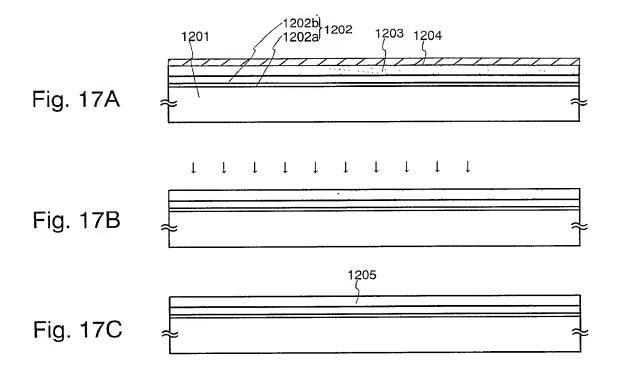


Fig. 16



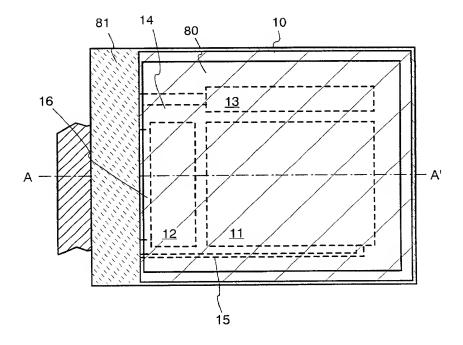


Fig. 18A

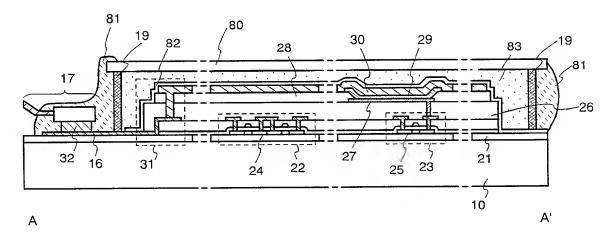
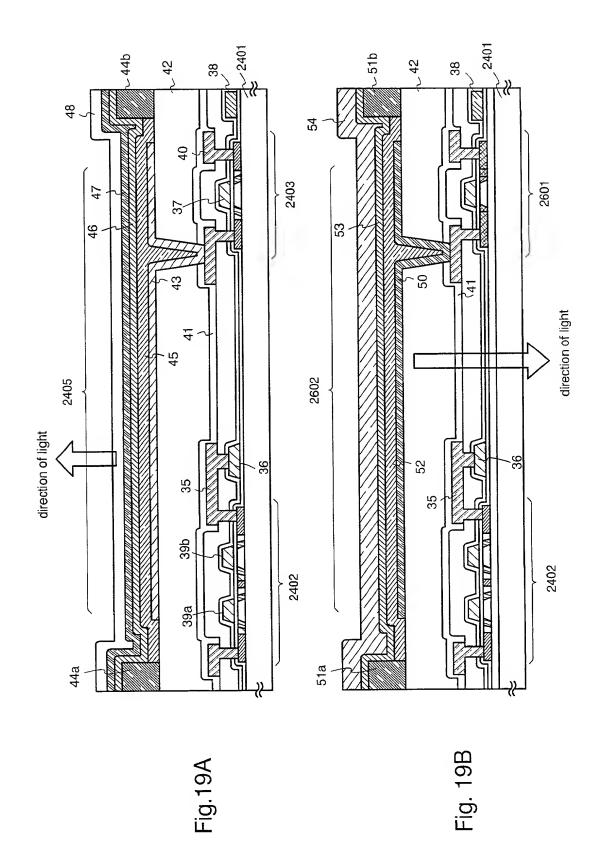
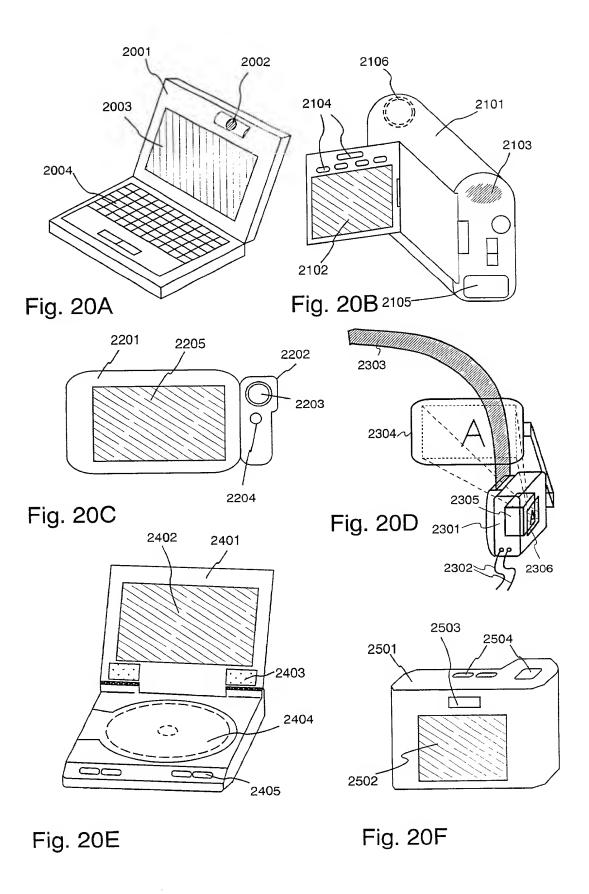


Fig. 18B





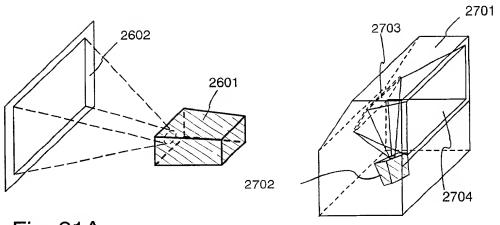


Fig. 21A

Fig. 21B

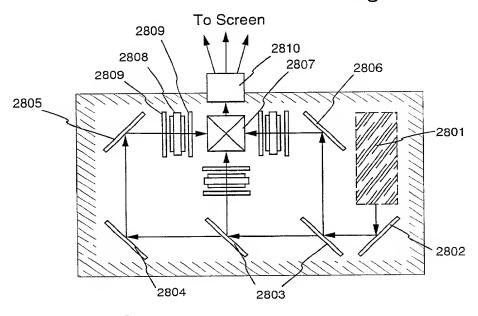


Fig. 21C

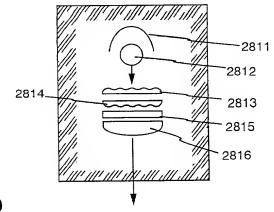
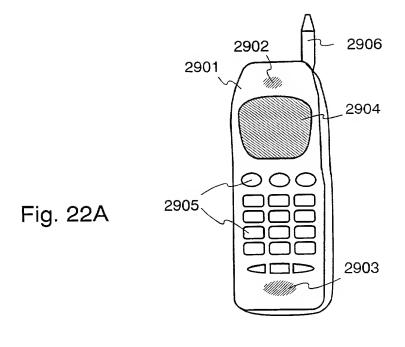
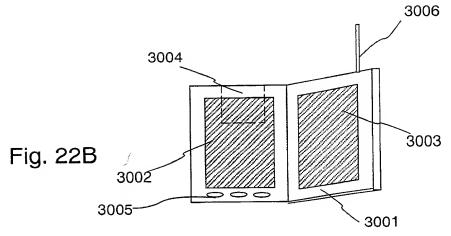
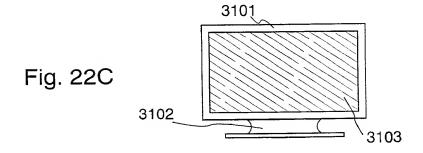


Fig. 21D







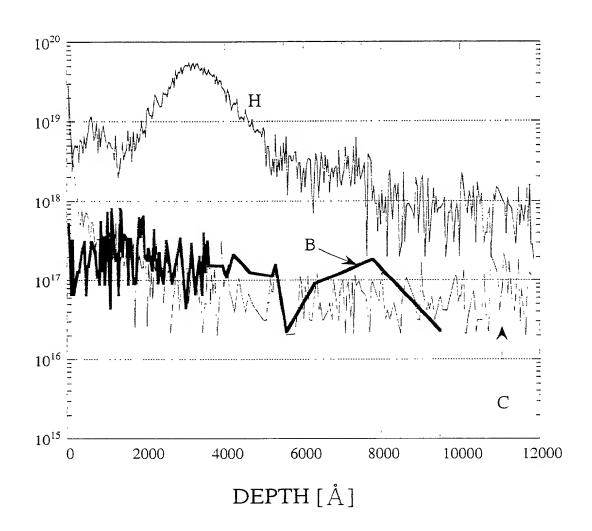


Fig. 23

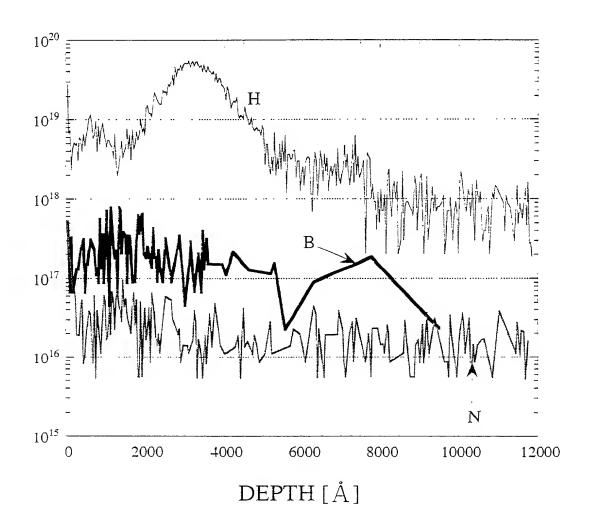


Fig. 24

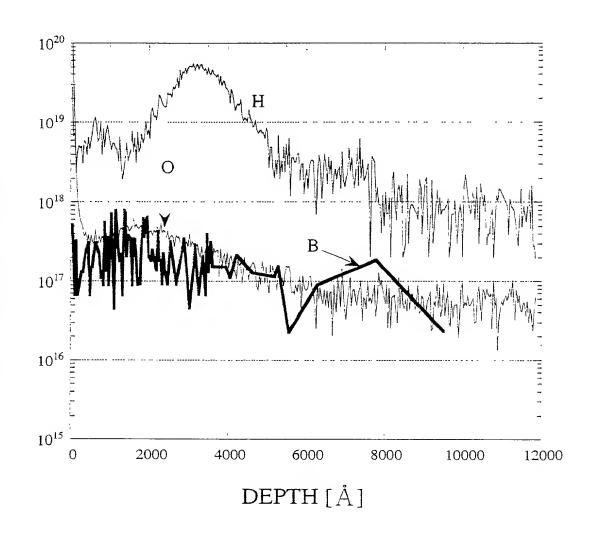


Fig. 25

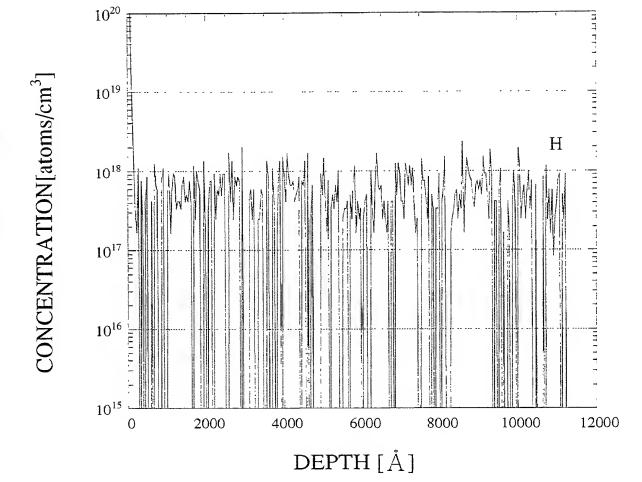


Fig. 26

CONCENTRATION[atoms/cm³-

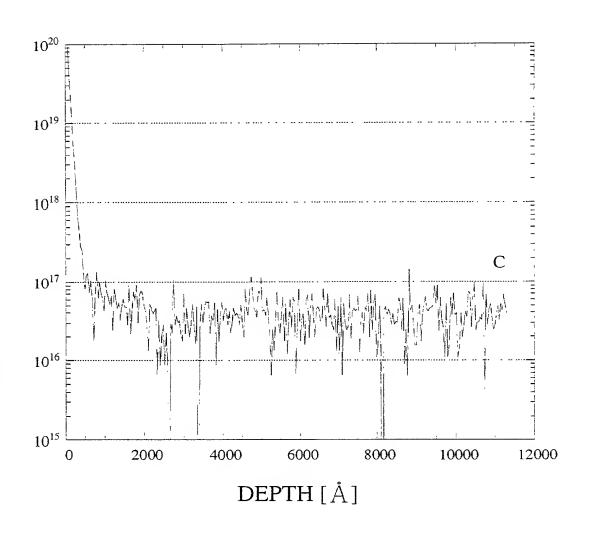


Fig. 27

11 MK 111

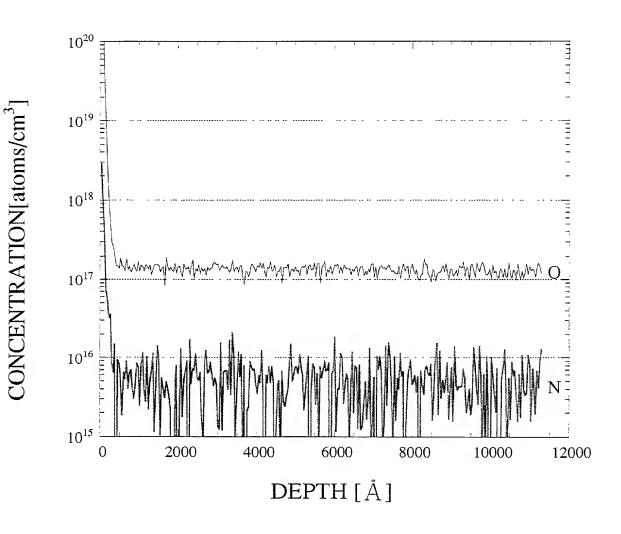
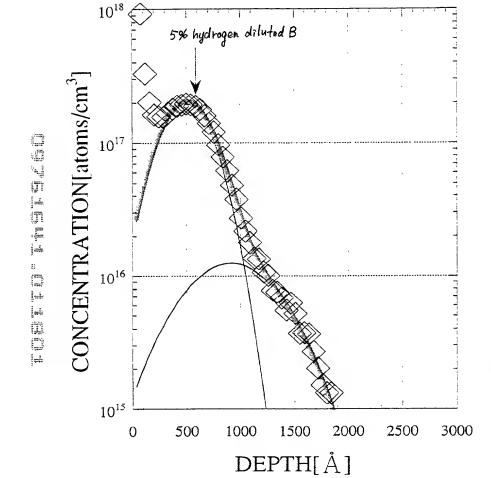


Fig. 28



	5% B fitting
	value
dosage 1	1.1224e+12
dosage 2	1.3183e+11
Standard deviation 1	227.08
Standard deviation 2	422.75
projected range1	494.37
Projected range 2	908.19
χ^2	0.52998
R	1

Gaussian function fitting projected range of B at 30kV (Å)
LSS calculation (into Si on 5202)
B⁺: ~ 1000 Å
B₂⁺: ~ 500 Å

Fig. 29

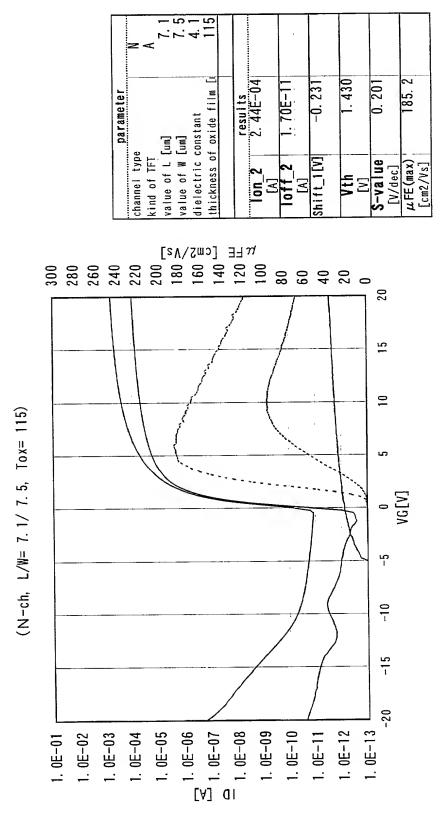


Fig. 30

results 2.65E-04 178.5 -1.0860.308 thickness of oxide film [nm 1.361 parameters dielectric constant value of L [um] channel type S-value [V/dec] \(\mu \) FE (max) [cm2/Vs] kind of TFT Shift_1[V] Off 2 300 280 260 220 220 140 [cm2/Vs] 100 80 60 40 20 0 20 15 10 (N-ch, L/W= 7.1/7.5, Tox= 115)VG[V] -10 -15 -20 1. 0E-10 1. 0E-12 1. 0E-13 1. 0E-05 1. 0E-09 1. 0E-11 1. 0E-02 1. 0E-03 1. 0E-04 1. 0E-01 1. 0E-06

Fig. 31